

DIMITRIS KAZAZIS

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Date of birth: 03 November 1978

Nationality: Greek

Married, 2 boys (twins)



Keywords: Nanofabrication, structural and electronic characterization, solid state physics, graphene and 2D systems, quantum Hall effect, magnetotransport, international profile.

Education

2005-2009	Brown University, School of Engineering Doctorate of Philosophy in Engineering, may 2009. Thesis : "Ultrathin Ge/high-k dielectric structures for end-of-roadmap devices and other applications." Advisor: A. Zaslavsky, Readers: J. R. Beresford, R. Zia.	Providence, RI, USA
2003-2005	Brown University, School of Engineering Master of Science in Engineering, may 2005.	Providence, RI, USA
1996-2001	National Technical University of Athens School of Electrical and Computer Engineering Diploma degree (5-year, MSc equivalent) in Electrical and Computer Engineering, July 2001.	Athens, Greece

Experience (Research)

2016-present	Paul Scherrer Institute Laboratory for Micro and Nanotechnology Scientific Project Coordinator/Researcher ▪ Scientific project coordination within the NFFA framework ▪ Advanced nanolithography techniques	Villigen, Switzerland
2015-2016	Paris Observatory Laboratory for Studies of Radiation and Matter in Astrophysics and Atmospheres (LERMA) Research Engineer (work conducted 100% at the Laboratory for Photonics and Nanostructures, CNRS-LPN) ▪ Development and nanofabrication of THz detector circuits for space applications.	Paris, France
2009-2014	National Center for Scientific Research (CNRS) Laboratory for Photonics and Nanostructures (LPN) Postdoctoral Researcher ▪ Nanofabrication and transport measurements of graphene devices, quantum Hall effect. ▪ Development, nanofabrication, and characterization of a state-of-the-art electrical resistance standard based on the quantum Hall effect in graphene. ▪ Design, fabrication, and characterization of suspended two dimensional electron-gas structures (electronic and thermodynamic applications, NEMS). ▪ Nanofabrication of electromagnetic antidote lattices in GaAs. ▪ Fabrication and characterization of a magnetic domain wall motion sensor (2DEG).	Marcoussis, France
2003-2009	Brown University, School of Engineering Research Assistant ▪ Design and fabrication of all-epitaxial ultrathin germanium-on-insulator (GeOI) devices. ▪ Transport measurements and characterization as a function of temperature. ▪ Physics of ambipolar and interband tunneling FET transistors. ▪ Modelling of nanoscale CMOS for probabilistic computation in the presence of noise.	Providence, RI, USA

Summer 2007	IBM T. J. Watson Research Center <i>Internship</i>	Yorktown Heights, NY, USA
Summer 2006	IBM T. J. Watson Research Center <i>Internship</i>	Yorktown Heights, NY, USA
2000-2002	National Technical University of Athens Microelectronic Circuit Design Group Research Associate	Athens, Greece

■ Design of a mass spectrometry measurement set-up for in-situ studies of photocatalytic oxidation on nanometer thick oxides in high vacuum.

■ In-situ experiments on the photocatalytic activity on ultrathin titanium oxide films.

■ Epitaxial growth of single crystal Ge on crystalline La-Y oxide on (111) Si.

■ Characterization and modelling of 0.15 µm CMOS transistors.

■ DC, CV, and RF measurements on deep submicron CMOS.

Experience (Teaching)

2013-2016	Université Paris Diderot – Paris 7	Paris, France
	■ Problem sections (travaux dirigés) for Physics (Mechanics).	

■ Student supervision: 2 Master students (Laboratory for Photonics and Nanostructures).

2003-2009	Brown University, School of Engineering	Providence, RI, USA
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■ Problem and lab sections: Analysis and design of electronic circuits; Introduction to semiconductors and semiconductor electronics; Electricity and magnetism.

■ Student supervision: 3 PhD students (clean room, magnetotransport, cryogenics).

Skills

Nanofabrication

- Extensive experience in nanofabrication and clean room work since 2003.
- Very experienced in electron beam lithography (EBL) for nanoscale patterning and photolithography (autonomous user of the Vistec EBLG 5000+ EBL system).
- Vacuum deposition techniques: Electron beam evaporation, sputtering, PECVD, ALD.
- Dry and wet etching techniques.
- Experience with ultrahigh vacuum (UHV) technology and systems and in cryogenics.
- Experience in molecular beam epitaxy (MBE).
- Wafer cleaning/cleaving techniques, dry/wet oxidation, annealing, wedge bonding, etc.

Material/Device Characterization

- Scanning electron microscopy (SEM).
- AFM, profilometry, ellipsometry, Raman spectroscopy.
- Electronic measurements, magnetotransport (superconducting magnet system, 1.3-300K).
- Hall effect characterization.

Computer Skills

- Very experienced in MATLAB and LabVIEW.
- Tanner EDA L-Edit Layout Editor and GenISys BEAMER software for e-beam lithography.
- Programming languages: C/C++.
- Software packages: COMSOL, Origin, Silvaco packages, IC-CAP modeling software, SPICE
- Other: UNIX, LaTex

Languages

- Greek (native), English (proficient), French (upper intermediate), Italian (intermediate).

Administrative Skills

- Scientific project management

Distinctions, Administrative Experience, and Interests

- Reviewer, ACS Nano Letters.
- Brown University prospective student interviewer, 2014-present.
- Dean's Fellowship, Brown University, 2003-2004; Efstratiou Fellowship, Greece 1996-2001.
- Award of excellence, Nationwide Chemistry Contest, Hellenic Union of Chemists, 1997.
- Microcontrollers, guitar, cooking, skiing, traveling, painting, electronic projects (drones).

Publications

14 international journal articles ; 1 book chapter ; several papers in conference proceedings.

- B. A. Piot, W. Desrat, D. K. Maude, D. Kazazis, A. Cavanna, and U. Gennser, "Disorder-induced stabilization of the quantum Hall ferromagnet", Phys. Rev. Lett. **116**, 106801 (2016).
- R. Ribeiro-Palau, F. Lafont, J. Brun-Picard, D. Kazazis, A. Michon, F. Cheynis, O. Couturaud, C. Consejo, B. Jouault, W. Poirier, and F. Schopfer, "Quantum Hall resistance standard in graphene devices under relaxed experimental conditions", Nature Nanotechnol. **10**, 965 (2015).
- F. Lafont, R. Ribeiro-Palau, D. Kazazis, A. Michon, O. Couturaud, C. Consejo, T. Chassagne, M. Zielinski, M. Portail, B. Jouault, F. Schopfer, and W. Poirier, "Quantum Hall resistance standard based on graphene grown by chemical vapor deposition on silicon carbide", Nature Commun. **6**, 6806 (2015).
- J. Schluck, S. Fasbender, T. Heinzel, K. Pierz, H. Schumacher, D. Kazazis and U. Gennser, "Snake orbit commensurability resonances in magneto-electric lateral superlattices", Phys. Rev. B **91**, 195303 (2015).
- B. Jabakhanji, D. Kazazis, W. Desrat, A. Michon, M. Portail, and B. Jouault, "Magnetoresistance of disordered graphene: from low to high temperatures", Phys. Rev. B **90**, 035423 (2014).
- B. Jabakhanji, A. Michon, C. Consejo, W. Desrat, M. Portail, A. Tiberj, M. Paillet, A. Zahab, F. Cheynis, F. Lafont, F. Schopfer, W. Poirier, F. Bertran, P. Le Fevre, A. Taleb-Ibrahimi, D. Kazazis, J. Camassel, and B. Jouault, "Tuning the transport properties of graphene films grown by CVD on SiC(0001) : effect of in-situ hydrogenation and annealing", Phys. Rev. B **89**, 085422 (2014).
- E. Pallecchi, M. Ridene, D. Kazazis, M. O. Goerbig, F. Schopfer, W. Poirier, D. Mailly, and A. Ouerghi, "Insulating to relativistic quantum Hall transition in disordered graphene", Sci. Rep. **3**, 1791 (2013).
- D. Kazazis, E. Bourhis, J. Gierak, O. Bourgeois, T. Antoni, and U. Gennser "Suspended two-dimensional electron and hole gases", Proceedings of the 31st International Conference on the Physics of Semiconductors (ICPS 2012), AIP Conf. Proc. **1566**, 249 (2013).
- E. Pallecchi, M. Ridene, D. Kazazis, C. Mathieu, F. Schopfer, W. Poirier, D. Mailly, and A. Ouerghi, "Observation of the quantum Hall effect in epitaxial graphene on SiC(0001) with oxygen adsorption", Appl. Phys. Lett. **100**, 253109 (2012).
- D. Kazazis, B. Schuler, M. Granada, U. Gennser, G. Faini, M. Cerchez, and T. Heinzel, "Sensing domain wall pinning in the longitudinal magnetoresistance of a two-dimensional electron gas", Superlattice Microst. **52**, 11 (2012).
- W. Van Den Daele, S. Cristoloveanu, E. Augendre, C. Le Royer, J.-F. Damlencourt, D. Kazazis, and A. Zaslavsky, "GeOI as a Platform for Ultimate Devices" in *Future Trends in Microelectronics: From Nanophotonics to Sensors and Energy*, edited by S. Luryi, J. Xu, and A. Zaslavsky, John Wiley and Sons, Inc., Hoboken, New Jersey (2010).
- F. C. Sabou, D. Kazazis, R. I. Bahar, J. Mundy, W. Patterson, and A. Zaslavsky, "Markov Chain Analysis of Thermally Induced Soft Errors in Nanoscale CMOS Circuits", IEEE Trans. Dev. Mater. **9**, 494 (2009).
- D. Kazazis, S. Guha, N. A. Bojarczuk, Z. Zaslavsky, and H.-C. Kim, "Substrate Fermi Level Effects in Photocatalysis on Oxides: Properties of Ultrathin TiO₂/Si Films", Appl. Phys. Lett. **95**, 064103 (2009).
- D. Kazazis, P. Jannaty, A. Zaslavsky, C. Le Royer, C. Tabone, L. Clavelier, and S. Cristoloveanu, "Tunneling Field-Effect Transistor with Epitaxial Junction in Thin Germanium-on-Insulator", Appl. Phys. Lett. **94**, 263508 (2009).
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- H. Li, J. Mundy, W. Patterson, D. Kazazis, A. Zaslavsky, and R. I. Bahar, "Thermally Induced Soft Errors in nanoscale CMOS circuits", IEEE International Symposium on Nanoscale Architectures, (NANOSARCH 2007), pp. 62-69 (2007).

-  D. Kazazis, A. Zaslavsky, E. Tutuc, N. A. Bojarczuk, and S. Guha, “*Negative Differential Resistance in Ultra-Thin Ge-On-Insulator FETs*”, *Semicond. Sci. Technol.* **22**, S1 (2007).
-  H. Li, J. Mundy, W. Patterson, D. Kazazis, A. Zaslavsky and R. I. Bahar, “*A Model for Soft Errors in the Subthreshold CMOS Inverter*”, *Workshop on System Effects of Logic Soft Errors (SELSE 2)* (2006).
-  E.J. Preisler, S. Guha, B.R. Perkins, D. Kazazis, A. Zaslavsky, “*Ultrathin Epitaxial Germanium on Crystalline Oxide Metal-Oxide-Semiconductor-Field-Effect Transistors*”, *Appl. Phys. Lett.* **86**, 223504 (2005).
-  D. M. Binkley, M. Bucher, and D. Kazazis, “*Guiding the Designer in Optimizing Analog CMOS Design*”, *Proceedings of the European Conference on Circuit Theory and Design (ECCTD)* , pp. I-8 – I-13, (2003).
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-  D. Kazazis, “*Characterization and Modeling of the MOS Transistor over the Continuum of Inversion Level and Channel Length*”, Diploma Thesis, NTUA, Athens, Greece, July 2001.